



ICPT

Program Overview

ICPT 2024

**International Conference on
Planarization / CMP Technology**

Kurhaus Wiesbaden • October 15–18, 2024
www.icpt2024.org

VDE VDI⁷ GMM

ICPT 2024 Program Overview

	Wednesday, October 16		Thursday, October 17		Friday, October 18
07:00–08:00	Registration	07:30–08:00	Registration	07:30–08:00	Registration
08:00–08:10	Opening Remarks	08:00–08:10	Presentation ICPT 2025	08:00–08:30	Keynote
08:10–08:40	Keynote	08:10–08:40	Keynote	08:30–09:55	SESSION 9 Defects, defect control and Post CMP cleaning (2)
08:40–10:05	SESSION 1 FEOL CMP	08:40–10:05	SESSION 5 Equipment & CMP consumables	09:55–10:25	<i>Coffee Break & Exhibiton</i>
10:05–10:35	<i>Coffee Break & Exhibiton</i>	10:05–10:35	<i>Coffee Break & Exhibiton</i>	10:25–11:50	SESSION 10 CMP fundamentals, modeling and simulation (2)
10:35–12:00	SESSION 2 BEOL & 3D CMP (1)	10:35–12:00	SESSION 6 BEOL & 3D CMP (2)	11:50–12:10	STUDENT PAPER AWARD
12:00–13:30	<i>Lunch Break & Exhibiton</i>	12:00–12:15	Award Ceremony	12:10–12:20	Closing Remarks
13:30–14:55	SESSION 3 CMP fundamentals, modeling and simulation (1)	12:15–13:30	<i>Lunch Break & Exhibitons</i>	12:20–13:20	<i>Lunch Break</i>
14:55–15:25	<i>Coffee Break & Exhibiton</i>	13:30–14:55	SESSION 7 Emerging technologies & Substrate polish	13:20	End of ICPT 2024
15:25–16:50	SESSION 4 Defects, defect control and Post CMP cleaning (1)	14:55–15:25	<i>Coffee Break & Exhibiton</i>		
16:50–18:20	POSTER SESSION 1	15:25–16:50	SESSION 8 Extra SESSION		
		16:50–18:20	POSTER SESSION 2		
		19:30–22:30	Conference Dinner		



The given times in the program schedule are according to the German Local Time (CEST)

Wednesday, October 16, 2024

07:00 - 08:00	Registration
08:00 - 08:10	Opening Remarks
08:10 - 08:40	Keynote Development and Implementation of a Data Ecosystem to enable End-to-End Advanced Predictive Manufacturing using AI <i>Dr. Saifi Usmani, Merck</i>
08:40 - 10:05	SESSION 1: FEOL CMP
08:40	Invited CMP Challenges and Opportunities for FDSOI with 28nm-ePCM advanced technologies and beyond <i>Aurore Durel, STMicroelectronics, France</i>
09:05	Effect of sugar alcohols on removal rate and ceria contamination as a function of carbon number in STI-CMP <i>Muskan Muskan, Jenasree Hazarika, Tae Hwan Kim, Tae Gon Kim, Jin Goo Park Hanyang University, Korea, Republic of (South Korea)</i>
09:25	Smart Design of A Novel Low Selective W CMP Slurry <i>Hongjun Zhou¹, Joon-Yeon Cho², Gary Lee², Jimmy Chang² ¹Merck; ²Merck</i>
09:45	Development of CMP slurry for carbon hard mask <i>Rung-Je Yang¹, Allison Hsu¹, Leo Huang¹, Nita Fan¹, Ping Hsu¹, Kenjiro Ogata², Koichiro Hosokawa² ¹DuPont, Taiwan; ²NITTA DuPont Incorporated</i>
10:05 - 10:35	Coffee Break & Exhibiton
10:35 - 12:00	SESSION 2: BEOL & 3D CMP (1)
10:35	Invited Chemical Mechanical Polishing: A Key Enabling Process for Hybrid Bonding <i>Laura Mirkarimi, Adeia, USA</i>
11:00	Study on environmentally sustainable corrosion inhibitor of Cu CMP <i>Jongyeong Jeon, Seungjun Oh, Juyeol Lee, Taesung Kim Sungkyunkwan University, Korea, Republic of (South Korea)</i>
11:20	Cu/SiCN CMP for enabling wafer to wafer hybrid bonding down to 400 nm pitch <i>Sven Dewilde, Steven Deckers, Nancy Heylen, Katia Devriendt imec vzw, Belgium</i>
11:40	The impact of temperature on copper slurry chemistry <i>Pengzhan Liu, Hyeonjeong Lee, Chaerin Park, Taesung Kim Sungkyunkwan University, Korea, Republic of (South Korea)</i>
12:00 - 13:30	Lunch Break & Exhibiton

Wednesday, October 16, 2024

13:30 - 14:55 **SESSION 3 – CMP fundamentals, modeling and simulation (1)**

13:30 **Invited**
History and Future of CMP Process Monitoring Technology
Yoichi Shiokawa, EBARA, Japan

13:55 **Secrets of the Stribeck Curve**
Leonard Borucki
Araca Inc., United States of America

14:15 **Pad-Abrasive-Wafer Interaction at Micro-Scale in Chemical-Mechanical Polishing**
Hyun Jun Ryu¹, Seounghee Yun¹, Ji-hun Jeong², Sanha Kim¹
¹KAIST, Korea, Republic of (South Korea); ²MIT, United States

14:35 **Accelerating finite element simulations with machine learning to predict interfacial pressures in real-time**
Tom Rothe^{1,3}, Andre Lauff², Alexey Shaporin^{1,3}, Peter Thieme², Mudassir Ali Sayyed^{1,3}, Knut Gottfried³, Jörg Schuster^{1,3}, Jan Langer³, Martin Stoll¹, Harald Kuhn^{1,3}
¹University of Technology Chemnitz, Chemnitz, Germany; ²Infineon Technologies Dresden GmbH & Co. KG, Dresden, Germany; ³Fraunhofer Institute for Electronic Nano Systems (ENAS), Chemnitz, Germany

14:55 - 15:25 *Coffee Break & Exhibiton*

15:25 - 16:50 **SESSION 4 – Defects, defect control and Post CMP cleaning (1)**

15:25 **Invited**
“Low Stress” Defect Activated p-CMP Cleaning Processes by Tuning the Molecular Structure of Additives
Jason J. Keleher, Lewis University, USA

15:50 **Scale Dependence of Particle Removal Efficiency in PVA Brush Scrubbing**
Somin Shin¹, Ji-hun Jeong², Hyun Jun Ryu¹, Sanha Kim¹
¹KAIST, Korea, Republic of (South Korea); ²MIT, United States

16:10 **Challenge for Tiny Defect Issues in Advanced Process**
Tetsuya Kamimura, Naoko Oouchi, Toru Tuchihashi, Akihiko Ohtsu, Atushi Mizutani
FUJIFILM, Japan

16:30 **Complete removal of positively-charged ceria particles by using alkaline sodium percarbonate aqueous cleaning solution**
Boao Ma, Wenlong Tang, Linyi Shen, Qiancheng Sun, Haijun Cheng, Xin-ping Qu
School of Microelectronics, Fudan University, China, People's Republic of China

16:50 - 18:20 **POSTER SESSION 1**

Thursday, October 17, 2024

07:30 - 08:00	Registration
08:00 - 08:10	Presentation ICPT 2025
08:10 - 08:40	Keynote Lithography roadmaps <i>Alberto Pirati, ASML, The Netherlands</i>
08:40 - 10:05	SESSION 5 – Equipment & CMP consumables
08:40	Invited Role of CMP in Enabling Heterogeneous Integration <i>Brian Brown, Applied Materials, USA</i>
09:05	Deep Learning Approaches to Predict Pad Durability in Copper Chemical Mechanical Planarization <i>Seunghwan Lee, Jaewon Lee, Pengzhan Liu, Hosin Hwang, Hyunho Kim, Taesung Kim</i> <i>Sungkyunkwan University, Korea, Republic of (South Korea)</i>
09:25	Effect of increased slurry dwell time on polishing performance <i>Conrad Guhl, Felix Köhler, Benjamin Lilienthal-Uhlig, Fraunhofer IPMS CNT, Germany</i>
09:45	Dishing Control for Nanotwinned Copper TSV Patterned Wafer CMP with Composite Soft Polishing Pad <i>Yueh-Hsun Tsai¹, Kai-Xiang Xiao¹, An-Chieh Cheng¹, Huy Le Nam Quoc¹, Eyob Messele Sefene¹, Chao-Chang A. Chen^{1,2}</i> ¹ Department of Mechanical Engineering, National Taiwan University of Science and Technology, Taiwan; ² CMP Innovation Center, National Taiwan University of Science and Technology, Taiwan
10:05 - 10:35	Coffee Break & Exhibiton
10:35 - 12:00	SESSION 6 – BEOL & 3D CMP (2)
10:35	Invited CMP: a key process for DTW Hybrid bonding integration <i>Emilie Bourjot, CEA-Leti, France</i>
11:00	Impact of CMP Slurry Additives on Copper Pad Corrosion and Surface Topography of Interest to Cu-Cu Hybrid Bonding <i>Seonwoo Go¹, Hazarika Jenasree¹, Arim Woo¹, Jum-Yong Park², Tae-Gon Kim¹, Jin-Goo Park¹</i> ¹ Hanyang University, Republic of Korea; ² Samsung Electronics Co., LTD, Republic of Korea
11:20	Impact of Dissolved Oxygen on Metal Corrosion in Post-CMP Cleaning for Advanced Logic Structures <i>Katrina Mikhaylichenko, Applied Materials, United States of America</i>
11:40	Investigation on the removal mechanism of amorphous carbon chemical mechanical polishing <i>Ziyang Wang, Pengzhan Liu, Seunghwan Lee, Jinhyoung Lee, Taesung Kim</i> <i>Sungkyunkwan University, Korea, Republic of (South Korea)</i>
12:00 - 12:15	Award Ceremony
12:15 - 13:30	Lunch Break & Exhibiton

Thursday, October 17, 2024

13:30 - 14:55

SESSION 7 – Emerging technologies & Substrate polish

13:30

Invited

Extreme wafer thinning process, and subsurface damage study for 3D integration

Rami Chukka, imec, Belgium

13:55

Novel Catalyst-Referred Etching Technology for Preparing Epi-Ready Silicon Carbide Substrates

Ara Philipossian¹, Yasa Sampurno¹, Tatsutoshi Suzuki², Kazuto Yamauchi³

¹ Araca, Inc., Tucson AZ, USA; ² Toho Koki Seisakusho Co., Ltd., Yokkaichi, Japan; ³ Osaka University, Osaka, Japan

14:15

High-efficiency GaN polishing by photoelectrochemical etching-assisted catalyst-referred etching

Daisetsu Toh¹, Kiyoto Kayao¹, Tatsuya Fukagawa¹, Jumpei Yamada¹, Kazuto Yamauchi², Yasuhisa Sano¹

¹ Department of Precision Science and Technology, Graduate School of Engineering, Osaka University, Osaka, Japan; ² OSAKA UNIVERSITY-RIKEN Center for Science and Technology, Osaka University, Osaka, Japan

14:35

CMP steps to enable NbTiN-based Superconducting Digital Logic

Bart Kenens¹, Ankit Pokhrel¹, Benjamin Huet¹, Daniel Perez Lozano¹, Jean-Philippe Soulie¹, Diziana Vangoidsenhoven¹, Yann Canvel¹, Vincent Renaud¹, Amey M Walke¹, Jasper Bizindavyi¹, Sara Iraci¹, Blake Hodges², Seifallah Ibrahim², Trent Josephson², Min-Soo Kim², Sabine O'Neal², Kevin Vandersmissen¹, Katia Devriendt¹, Quentin Herr^{1,2}, Zsolt Tokei¹, Anna Herr^{1,2}

¹ imec, Belgium; ² imec Florida, USA

14:55 - 15:25

Coffee Break & Exhibiton

15:25 - 16:50

SESSION 8 – Extra SESSION

15:25

Invited

Innovative CMP technology for the next generation VNAND devices

KiHoon Jang, Samsung R&D Center, Korea

15:50

Surface polishing of polycrystalline silicon carbide using catalyst-referred etching

Yusuke Yoshida¹, Kiyoto Kayao¹, Daisetsu Toh¹, Jumpei Yamada¹, Kazuto Yamauchi², Yasuhisa Sano¹

¹ Department of Precision Science and Technology, Graduate School of Engineering, Osaka University, Japan; ² OSAKA UNIVERSITY-RIKEN Center for Science and Technology, Osaka University, Osaka, Japan

16:10

Nanoscale Dishing and Selectivity Control in STI Pattern Wafer via Mechano-Structural Heterogeneity of CeO₂ Nano Particle

Chulwoo Bae, Jinhyoung Lee, Juyong Lee, Jaedo Nam, Taesung Kim

Sungkyunkwan Univ., Korea, Republic of (South Korea)

16:30

Application of Neural Network Potential Molecular Dynamics Simulation to Atomic-scale understanding of silicon nitride CMP Process by Nano-sized ceria abrasive

Yoshishige Okuno, Ken Takahashi, AKIhiro Orita, Satoyuki Nomura

Resonac / Japan, Japan

16:50 - 18:20

POSTER SESSION 2

19:30 - 22:30

Conference Dinner

Friday, October 18, 2024

07:30 - 08:00	Registration
08:00 - 08:30	Keynote Challenges for hetero integration process technology, test and reliability <i>Prof. Harald Kuhn, Fraunhofer ENAS, Germany</i>
08:30 - 09:55	SESSION 9 – Defects, defect control and Post CMP cleaning (2)
08:30	Invited Evolution and progress of post CMP cleaning solution for defect reduction <i>Yuchun Wang, Anji Microelectronics Technology Ltd., China</i>
08:55	A Study on Evaluating Supercritical CO2 Cleaning with Pressure Pulse using Computational Fluid Dynamics <i>JooHwan Ha¹, Geumji Back¹, Jongyeong Jeon², Taesung Kim^{1,2,3}</i> <i>¹Department of Semiconductor Convergence Engineering, Sungkyunkwan University(SKKU), Suwon 16419, Republic of Korea; ²School of Mechanical Engineering, Sungkyunkwan University(SKKU), Suwon 16419, Republic of Korea; ³SKKU Advanced Institute of Nanotechnology(SAINT), Sungkyunkwan University(SKKU), Suwon 16419, Republic of Korea</i>
09:15	Separate Distance Measurement of Moving Nano-Particle from Surface in Wet Process using Astigmatism Defocus above Evanescent Field Range <i>Norita Kuroe¹, Panart Khajornrungruang¹, Yu Arima¹, Satomi Hamada², Yutaka Wada², Hirokuni Hiyama², Tomoya Nishi²</i> <i>¹Kyushu Institute of Technology, Japan; ²Ebara corporation, Japan</i>
09:35	Investigation of the Cross-Contamination Mechanism by PVA Brush Scrubbing Process and Parameters during Post-CMP Cleaning <i>Kwang-Min Han¹, Sumit Kumar², Mir Jalal Khan², Jae-Hyeong Lee², Tae-Gon Kim³, Jin-Goo Park²</i> <i>¹Department of Bio-Nano Technology, Hanyang University ERICA, Republic of Korea; ²Department of Materials Science and Chemical Engineering, Hanyang University ERICA, Republic of Korea; ³Department of Smart Convergence Engineering, Hanyang University ERICA, Republic of Korea</i>
09:55 - 10:25	Coffee Break & Exhibiton

Friday, October 18, 2024

10:25 - 11:50

SESSION 10 – CMP fundamentals, modeling and simulation (2)

10:25

Invited

First ten (of hundreds) ways to kill slurry quality

Rob Rhoades, X-Trinsic, USA

10:50

Exploring the Potential of Machine Learning in Developing CMP Slurry Composition

Akihiro Orita, Satoyuki Nomura, Resonac Corporation

11:10

Wafer Bonding Hotspots Detection by Chip-Scale CMP Simulation

Ruben Ghulghazaryan¹, Davit Piliposyan¹, Jeff Wilson², Ushasree Katakamsetty³, Yong Chau Ng³, Yudi Setiawan³, Anthony Villalon³, Sam Nakagawa³, Stefan Nikolaev Voykov³

¹Siemens Industry Software, Armenia; ²Siemens EDA, USA; ³GLOBALFOUNDRIES

11:30

Analysis of lower structures of asperities on pad surface

Yohei Hashimoto¹, Hozumi Yasuda², Norikazu Suzuki³

¹Kanazawa University, Japan; ²Ebara Company, Japan; ³Chuo University, Japan

11:50 - 12:10

STUDENT PAPER AWARD

12:10- 12:20

Closing Remarks

12:20 - 13:20

Lunch Break & Exhibiton

13:20

End of ICPT 2024

ICPT 2024 Poster session List

Wednesday, October 16, 2024

16:50 - 18:20 **POSTER SESSION 1**

- P1 **Cu-CMP Scratch reduction using by Temperature Control Rinse(TCR)**
Taketo Sekine, Applied Materials, United States of America
-
- P2 **A Novel Data-Driven Modeling based on Pad Surface Recognition for Predicting Material Removal Rate in CMP**
Jongmin Jeong¹, Yeongil Shin¹, Seunghun Jeong¹, Seonho Jeong¹, Masashi Kabasawa², Yoichi Shiokawa², Keita Yagi², Hozumi Yasuda², Jichul Yang², Katsuhide Watanabe², Yutaka Wada², Hirokuni Hiyama², Haedo Jeong¹
¹ Pusan National University, Busan, Republic of Korea;
² EBARA Corporation, Fujisawa, Kanagawa 251-8502, Japan
-
- P3 **Observation of liquid movement due to PVA brush nodule deformation and prediction of liquid transfer map**
Makoto Miwa¹, Shota Suzuki¹, Satomi Hamada², Toshiyuki Sanada¹
¹ Shizuoka University; ² Ebara Corporation
-
- P4 **Study on the Effect of High Temperature on Defects in Tungsten Chemical Mechanical Planarization**
Jeongyeol Yu^{1,2}, Taesung Kim²
¹ Samsung Electronics, Korea, Republic of (South Korea); ² Sungkyunkwan University, Korea, Republic of (South Korea)
-
- P5 **Preparation of a highly smoothed Si surface via catalyst-referred etching**
Yohei Miyaji¹, Kiyoto Kayao¹, Daisetsu Toh¹, Jumpei Yamada¹, Kazuto Yamauchi², Yasuhisa Sano¹
¹ Department of Precision Science and Technology, Graduate School of Engineering, Osaka University, 2-1 Yamadaoka, Suita, Osaka, Japan; ² Osaka University-RIKEN Center for Science and Technology
-
- P6 **A Novel Approach to Improve Cleaning Performance of High Oxide Rate CMP by Alkaline Ceria Slurry**
Yang-Yao Lee, Ming-Che Ho, Vibrantz Technologies, United States of America
-
- P7 **Investigation of silica particle and Mo ion contamination on PVA brush during Mo post-CMP cleaning process**
SUMIT KUMAR¹, PALWASHA JALALZAI¹, NAYOUNG KANG¹, TAE-GON KIM², JIN-GOO PARK¹
¹ Department of Materials Science and Chemical Engineering Hanyang University ERICA, Korea;
² Department of Smart Convergence Engineering, Hanyang University ERICA, Korea
-
- P8 **Stagnation Time Effects on Through-Silicon Via (TSV) Mechanical Reliability: A Study on Cu Corrosion Standards**
JINSOO YOON¹, Taesung KIM²
¹ Samsung Electronics Semiconductor, Hwaseong, Republic of (South Korea);
² Sungkyunkwan University, Korea, Republic of (South Korea)
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- P9 **High-Resolution Size Distribution Characterization of CMP Slurry Particles**
Andrea Tiwari¹, Daniel Troolin¹, Torsten Tritscher², Atul Patel¹, Justin Koczak¹, Nathan Birkeland¹, Hee-Siew Han¹
¹ TSI Incorporated, Shoreview, MN, United States of America; ² TSI GmbH, Aachen, Germany
-
- P10 **Performance of Novel DLC-Coated Conventional Gritted Diamond Discs in ILD CMP**
Yasa Sampurno¹, Len Borucki¹, Akira Okabe², Ara Phillipossian¹
¹ Araca, Inc., Tucson AZ, USA; ² Epicrew Corporation, Omura-city, Japan
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- P11 **Inline Real-Time Process Monitoring of CMP Slurries with Ultrasonic and Conductivity Measurements**
Raymond Maas, Rhosonics, The Netherlands

Wednesday, October 16, 2024

- P12 **Study on Property Changes Through Slurry Filtration**
Jongwoo Kwon^{1,2}, Taesung Kim³
¹ Samsung Electronics, Korea, Republic of (South Korea); ² Department of Semiconductor and Display Engineering, Sungkyunkwan University, Suwon, Republic of Korea; ³ School of Mechanical Engineering, Sungkyunkwan University, Suwon, Republic of Korea
-
- P13 **Planarization of substrate with metal wiring using catalyst-referred etching – Etching characteristic of wiring metal –**
Hiroto Yamasaki¹, Kiyoto Kayao¹, Daisetsu Toh¹, Jumpei Yamada¹, Kazuto Yamauchi², Yasuhisa Sano¹
¹ Department of Precision Science and Technology, Graduate School of Engineering, Osaka University, Osaka, Japan; ² OSAKA UNIVERSITY-RIKEN Center for Science and Technology, Osaka University, Osaka, Japan
-
- P14 **Investigation of the root cause of the scratch formation during copper post-CMP brush scrubbing**
MAHEEPAL YADAV¹, SANJAY BISHT¹, SE-HOON PARK¹, TAE-GON KIM², SATOMI HAMADA³, JIN-GOO PARK¹
¹ Department of Materials Science and Chemical Engineering, Hanyang University, Ansan, 15588, Korea; ² Department of Smart Convergence Engineering, Hanyang University, Ansan, 15588, Korea; ³ EBARA Corporation, Fujisawa, Kanagawa, 251-8502, Japan
-
- P15 **Influence of a rolling brush on the fluid flow and concentration distribution of cleaning solutions on a rotating disk**
Yoshinori Jinbo¹, Nao Okuma², Eri Okubo², Yasushi Hongo², Toshimasa Mano², Toshiyuki Sanada¹
¹ Shizuoka University, Japan; ² AION Co., Ltd., Japan
-
- P16 **Reduction of Large Particles and Small Particles in Colloidal Silica Manufacturing Process**
Chiharu Nakano, Shunsuke Tanaka, Haruhiko Eki, Shun Arai, Shuta Ozawa
FUSO Chemical CO. LTD., Japan
-
- P17 **Influence of Pad-Wafer-Silica based Slurry Interface on BSI Performances**
Victor Soty¹, Cédric Perrot¹, Aurore Bonnevalle², Cassandre Maljournal², Elodie Bêche², Sébastien Mermoz², Catherine Euvrard¹
¹ Univ. Grenoble Alpes, CEA, LETI, 38000 Grenoble, France; ² ST Microelectronics, France
-
- P18 **Silicon Oxide and Tungsten Compatible Formulation for Ceria and Metal Ion Removal for Post-CMP Clean**
Ping Tzeng¹, Katie M. Gramigna², Yuwan Juan¹, Ling Chang¹, Ian Hung¹, Ping Hsu¹
¹ DuPont, Hsinchu site 1 (TW); ² DuPont, Newark (US)
-
- P19 **Investigating Foreign Materials in Post CMP Cleaning Modules with Total Holographic Characterization**
Laura A Phillips¹, Fook Chiong Cheong¹, Tiffany Markus¹, Yongneng Wu², Nai-Chieh Huang², Max Gauge², Jianshe Tang²
¹ Spheryx, Inc., United States of America; ² Applied Material, United States of America
-
- P20 **Quantitative measurement of emulsion droplets in silica CMP slurries with Total Holographic Characterization**
Laura Phillips, Fook Chiong Cheong, Tiffany Markus, Spheryx, Inc., United States of America
-
- P21 **Development of model-based robot polishing system - Measurement of robot rigidity distribution and its application -**
Kotaro Totsuka¹, Takamasa Yamamoto², Michio Uneda¹, Norikazu Suzuki³
¹ Kanazawa Institute of Technology; ² Yamamoto Metal Technos Co.,Ltd.; ³ Chuo University
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- P22 **Advanced Copper Post-CMP Cleaning Formulation Providing Superior Copper Compatibility and Ruthenium Residue Removal Capability**
Peter Sun, Jacky Cheng, Ping Hsu, DuPont, Taiwan
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Wednesday, October 16, 2024

- P23 **Functionalized Water Production Methods using Membrane Contactors and its effect on Particle Removal Efficiency post CMP**
Joel Cardona, Sang-Hyeon Park, Charlotte M Starnes, Solventum, United States of America
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- P24 **Research on Bio-based CMP Pads to Reduce Carbon Dioxide Emissions**
Mingyeong Ji, Jongwook Yoon, Jangwon Seo, SK enpulse, Korea, Republic of (South Korea)
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- P25 **Effect of Surface Oxidation on post-Chemical Mechanical Planarization Cleaning of Silicon Carbide**
Piper M. Smith, Jason J. Keleher, Lewis University, United States of America
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- P26 **Oxide CMP Material Removal Rate Performance based on a smart material properties study**
Aurore Bonneville Durel¹, Max Bastien¹, Floriane Demeyer¹, Valérie Dupuy¹, Camille Sgrillo¹, Jeanny Maurice¹, Cédric Perrot², Victor Soty², Catherine Euvrard², Daniel Benoit¹, Sébastien Petitdidier¹
¹ STMicroelectronics, France; ² Univ. Grenoble Alpes, CEA, LETI, 38000 Grenoble, France
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- P27 **Extending the applicability of a novel cleanliness assessment method for CMP slurries**
Jochen Ruth, Oliver Baatz, Pall GmbH, Germany
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- P28 **Post-CMP cleaning of silicon-germanium wafer surfaces**
Andreas Krüger, Awwal Adeniyi Adesunkanmi, Rasuole Lukose, Yuji Yamamoto, Wei-Chen Wen, Marco Lisker, IHP GmbH - Leibniz-Institut für innovative Mikroelektronik, Germany
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- P29 **Enhanced Organic Residue Removal during Cu post-Chemical Mechanical Planarization (p-CMP) Cleaning via surface active non-covalent complexes**
Katey M. Sheets, Jason J. Keleher, Lewis University, United States of America
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- P30 **Toward an optimized method to remove edge epi defects for GaN on Silicon growths**
IATOSTI Christophe¹, BENSALÉM Salma², ROY Emmanuel¹, CHABOUREL Alain², KODERA Kenji³, HONG Victor³, NAKANISHI Masayuki³
¹ STMicroelectronics, 153 rue des Douets 37100 Tours, France;
² Ebara Precision Machinery Europe GmbH, 26 Av Jean Kuntzmann, 38330 Montbonnot St Martin, France;
³ Ebara Corporation, 4-2-1, Honfujisawa, Fujisawa-shi, 251-8502, Japan
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- P31 **Regulating molybdenum dissolution through controlled oxide phase formation in CMP with catalytic oxidation**
Bobae Lee, Memory CMP Technology Team, Samsung Electronics, Pyeongtaek, South Korea
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- P32 **Advanced Filtration Solution for LPC Removal Efficiency Enhancement in CMP Applications**
Alan {Ling-Hsiang} Chao, Enzo Chen, Henry Wang, Entegris, Taiwan
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- P33 **Optimizing Wafer Polishing: Innovations in CMP Techniques and Filtration**
Chloe {Ting Chen} Chen, Jason {Yu Chieh} Fu, Nathan Hou, Nate Chang, Elaine Wu, Alex Chuang Entegris, Inc.
-
- P34 **Exploring the Potential of Precision Engineering in Next-Generation CMP Consumables**
Yi He, 3M, United States of America
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Thursday, October 17, 2024

16:50 - 18:20 **POSTER SESSION 2**

- P35 **Application of Neural Network Potential Molecular Dynamics Simulation to Atomic-scale understanding of poly-Si CMP Process by Nano-sized ceria abrasive**
Ken Takahashi, Yshishige Okuno, Akihiro Orita, Satoyuki Nomura, Resonac / Japan, Japan
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- P36 **Clarification of Polishing Mechanism Focusing on Polishing Pad in CMP**
Syuhei Kurokawa¹, Hirokuni Hiyama², Yutaka Wada², Hozumi Yasuda², Shuntaro Hayashi²
¹ Kyushu University, Japan; ² EBARA CORPORATION
-
- P37 **Maximizing Material Removal Efficiency of Micro-Structured Pads in Chemical Mechanical Polishing**
Seounghee Yun, Hyun Jun Ryu, Sanha Kim, Korea Advanced Institute of Science and Technology, Korea, Republic of (South Korea)
-
- P38 **Enabling Fast Boron Doped Polysilicon Removal by the Advanced Oxidation and Enhanced Mechanical Approach for DRAM Scaling**
Yang-Yao Lee, Ming-Che Ho, Vibrantz Technologies, United States of America
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- P39 **A prediction model of material removal rate distribution considering slurry supply position and relative motion**
Takumi Sato^{1,3}, Yuki Watanabe¹, Yohei Hashimoto², Norikazu Suzuki³
¹ Ebara Corporation, Japan; ² Kanazawa University, 9201192 ishikawa, Japan; ³ Chuo University, 1128551, Tokyo, Japan
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- P40 **Fundamentals in Polishing Scratch Reduction through Advanced CMP Pad Conditioning Processes**
Yongsik Moon¹, Kyoung-Kuk Kwack¹, Joohan Lee¹, Jongkuk Park¹, Eunhwa Song¹, Youngtae Jeon¹, Joohee Lee¹, Sungyu Park¹, Yujeong Jin¹, Jongjae Lee¹, Yongik Whang²
¹ EHLA Diamond, 374 Nambu-daero, Osan-si, Gyeonggi-do, Republic of Korea; ² EHLA Europe GmbH, Rudolf-Diesel-Straße 7, 65760 Eschborn, Germany
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- P41 **Influence of Deposition Technique (ALD vs.PVD) on Surface Properties of Mo during Post-CMP Cleaning**
Nayoung Kang¹, Palwasha Jalalzai¹, Tae-Gon Kim², Jin-Goo Park¹
¹ Department of Materials Science and Chemical Engineering Hanyang University ERICA, Korea; ² Department of Smart Convergence Engineering, Hanyang University ERICA, Korea
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- P42 **Study of chemical reactions for development of a novel CMP process using a supercritical carbon dioxide as a solvent**
Seokchan Lee¹, Ju Yong Lee², Chulwoo Bae¹, Kihong Park², Jeongyong Bae², Taesung Kim^{1,2}
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- P43 **A data driven approach for real-time estimation of material removal rate toward advanced CMP process control**
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- P44 **Copper Oxidation Mechanism by CMP Slurry Containing Ceria Abrasives**
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² Samsung Electronics, Korea, Republic of (South Korea)
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- P46 **Fast STI-CMP process characterization for diverse layouts by dedicated testchips and high throughput AFM-WLI metrology**
Conrad Guhl¹, Victor Bergmann², Hongwei Ma³, Benjamin Lilienthal-Uhlig¹
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- P47 **Polymer/Cu CMP using Ultrafine α -alumina Slurry for Chiplet Applications**
Yutetsu Kamiya¹, Yuzo Nakamura^{1,2}, Kohei Nakayama¹, Kenta Hayama¹, Fumihiro Inoue¹
¹ Yokohama National University, Japan; ² Mitsui Chemicals, Inc., Japan
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- P48 **Development of monitoring function of fine particle unit of chemical mechanical polishing process**
Chanho Park^{1,2}, Changmin Kim^{1,2}, Kihong Park², Sanghyuck Jeon^{1,2}, Hyunho Seok³, Taesung Kim^{2,3}
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David Earl Slutz, DS Technical Consultant LLC, United States of America
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Jaewon Lee, Gyuyoung Lee, Seunghwan Lee, Taesung Kim
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- P51 **Silica particle contamination and removal mechanism in Molybdenum post-CMP cleaning**
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Yinuo Jin, David Wang, Jian Wang, Minxu Li, ACM Research, Inc., People's Republic of China
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Elizabeth M. McDonnell, Jason J. Keleher, Lewis University, United States of America
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- P54 **The role of chemical reactions in oxide film polishing**
Chaerin Park, Pengzhan Liu, Hyeonjeong Lee, Taesung Kim
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- P55 **Effect of mixed abrasive particle size according to number concentration ratio on W CMP**
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- P56 **Uniformity-improved Chip Thinning by CMP for Failure Analysis**
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- P58 **Advances of Alkaline Oxide CMP Process: Efficiency, Versatility, and Synergy**
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Zhenyang Wang, Tongqing Wang, Xinchun Lu, State Key Laboratory of Tribology, Tsinghua University
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Lifei Zhang, Tongqing Wang, Yuhong Liu, Xinchun Lu, Tsinghua University, China, People's Republic of
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DuPont Taiwan Limited, Taiwan
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Liang Jiang, Southwest Jiaotong University, China, People's Republic of
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Jaedong Lee, KCTech, Korea, Republic of (South Korea)
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Shinsuke Matsui¹, Haruki Kosuge¹, Takahiko Mitsui², Takahiro Shimada², Toshiyasu Yajima³, Daisuke Ninomiya³, Dai Nadahara³
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Majid Entezarian, John Morby, Pierre Alexandre Bourgeois, Solventum, United States of America
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Kangchun Lee, Kyonggi University, Korea, Republic of (South Korea)
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